Silicon PNP Power Transistors 2SA1304

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DESCRIPTION

- ·With TO-220Fa package
- ·Complement to type 2SC3296
- ·High breakdown voltage

APPLICATIONS

- ·Power amplifier applications
- ·Vertical output applicatios

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

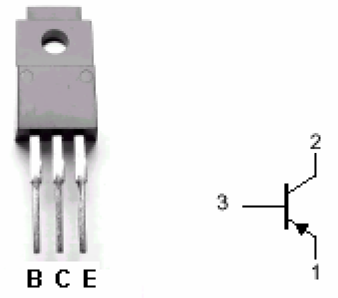

Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1.5	A
I_B	Base current		-0.5	A
P_C	Collector power dissipation	T_C=25□	20	W
		T_a=25□	2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA , I_B=0	-150			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-500mA; I_B=-50mA			-1.5	V
V_{BE}	Base-emitter on voltage	I_C=-500mA ; V_{CE}=-10V			-0.85	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V;I_E=0			-10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-10	μA
h_{FE}	DC current gain	I_C=-500mA ; V_{CE}=-10V	40		140	
C_{ob}	Output capacitance	I_E=0; V_{CB}=-10V,f=1MHz		55		pF
f_T	Transition frequency	I_C=-500mA ; V_{CE}=-10V		4		MHz

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PACKAGE OUTLINE

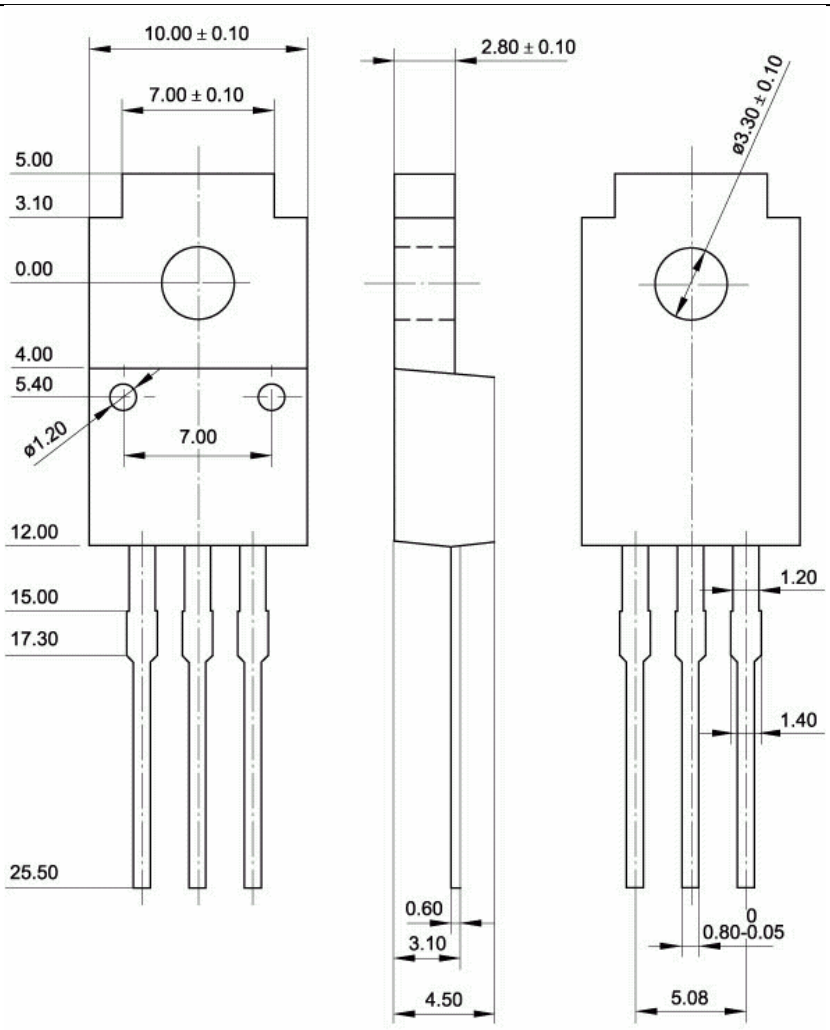

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)

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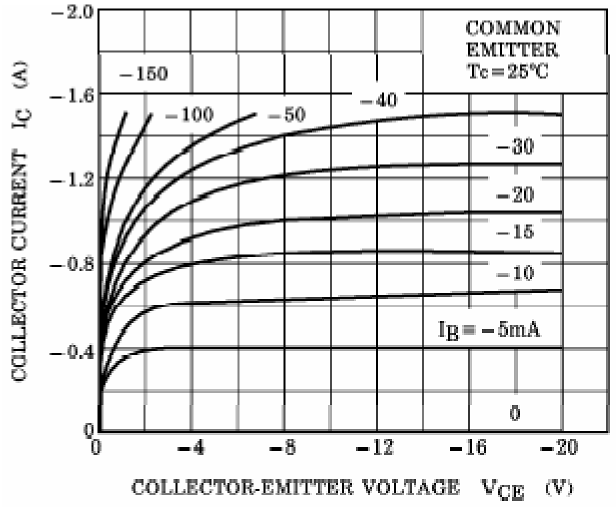

Fig.3 Static Characteristic

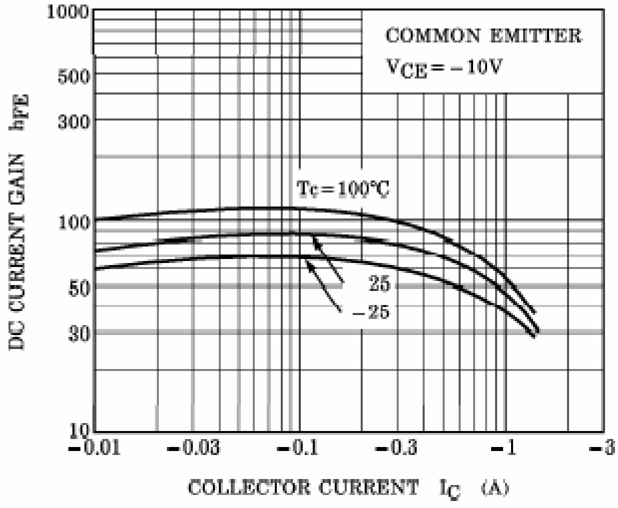

Fig.4 DC current Gain

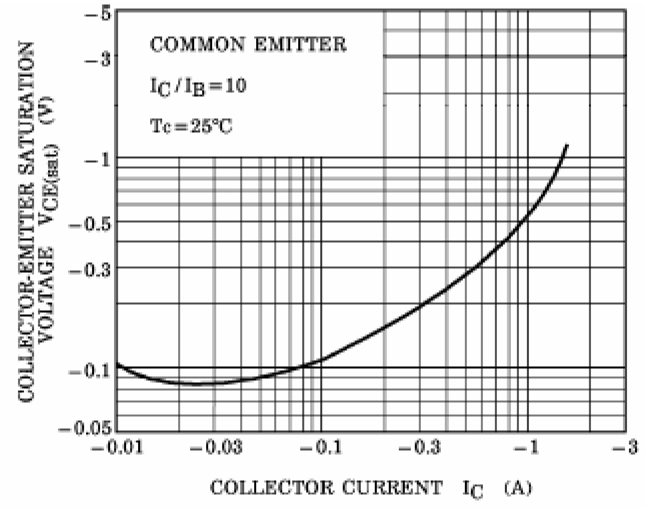

Fig.5 Collector-Emitter Saturation Voltage

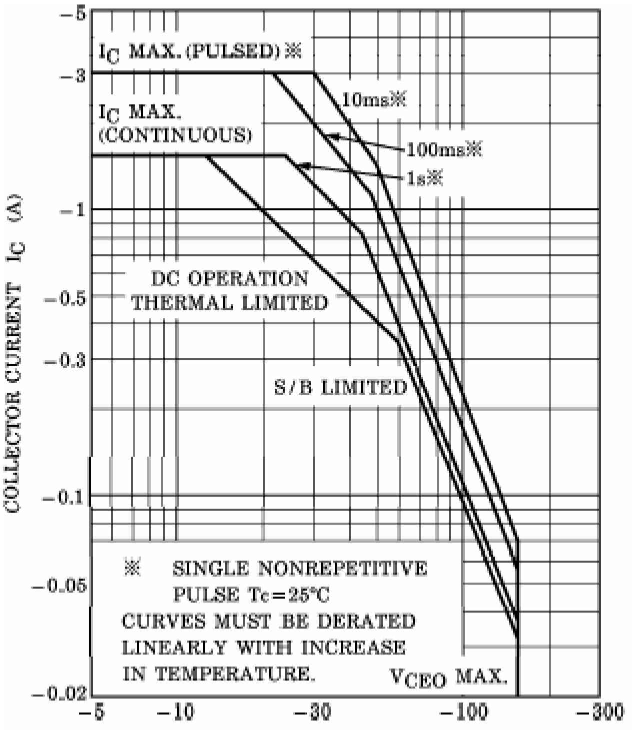

Fig.6 Safe Operating Area

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